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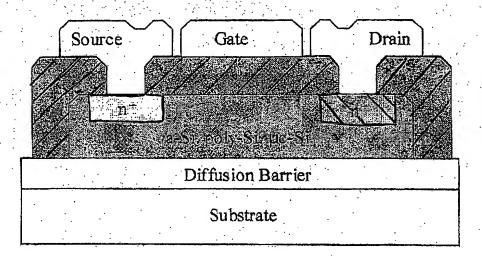
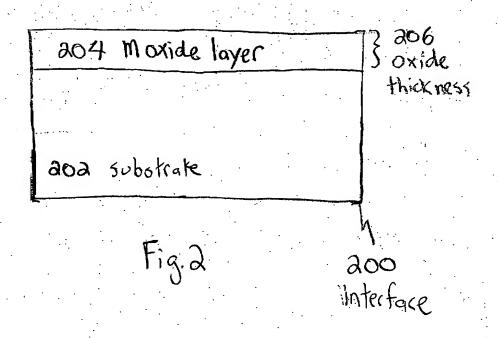
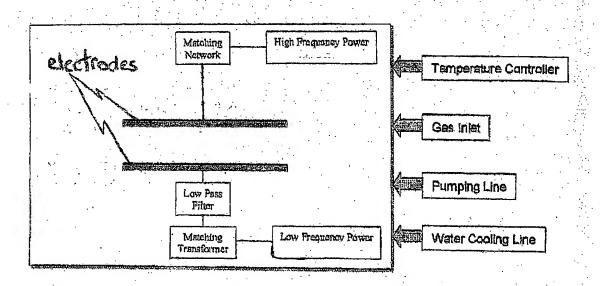


Fig. 1 (prior art)





F19.3

406 Oxide layer

404 Siliconlayer

402 substrate

Fig. 4

Tpen (°C)	(°C) d (A) Plasma		V _{FB} (V) N _f (cm ⁻²)		cm ⁻²)	Dit (cm-2 eV-1)	J (A/cm2)	E (MV/cm)		EBD (MV/cm)		
	· ,	Oxidation			(x10	cm-2)	(x10 ¹⁰ cm-2 eV-1)	(at 2 MV/cm)	(at J=10	* A/cm*)	(Physici	ai)
150	500	As-Dep	ŀ	-7.5		26.0	3.5	1.80E-07		4.3		6.8
150	500	He/O2		-0.8	1.11	1.8	1.2	2.60E-08		6.4		7.2

TABLE 1

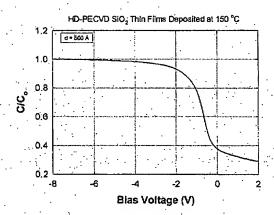
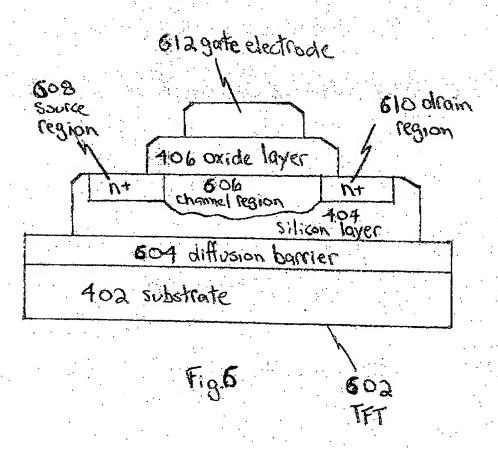


TABLE 2

Fig.5



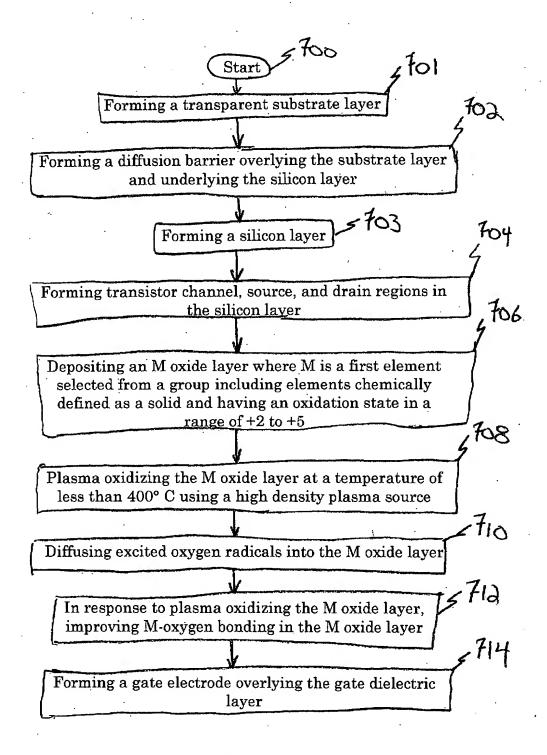


Fig. 7

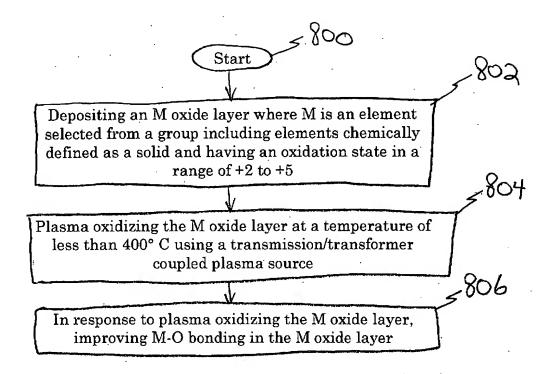


Fig. 8

In a film processing chamber, depositing an M oxide layer where M is an element selected from a group including elements chemically defined as a solid and having an oxidation state in a range of +2 to +5

Leaving the M oxide layer in the film processing chamber, plasma oxidizing the M oxide layer at a temperature of less than 400° C using a high density (HD) plasma source

In response to plasma oxidizing the M oxide layer, improving M-O bonding in the M oxide layer

Fig. 9